ABSTRACT OF THE DISCLOSURE

A semiconductor device includes a thin film transistor including a semiconductor layer that includes a channel region, a source region and a drain region, a gate insulating film provided on the semiconductor layer, and a gate electrode for controlling the conductivity of the channel region, wherein the surface of the semiconductor layer includes a minute protruding portion, and the side surface inclination angle of the gate electrode is larger than the inclination angle of the protruding portion of the semiconductor layer.